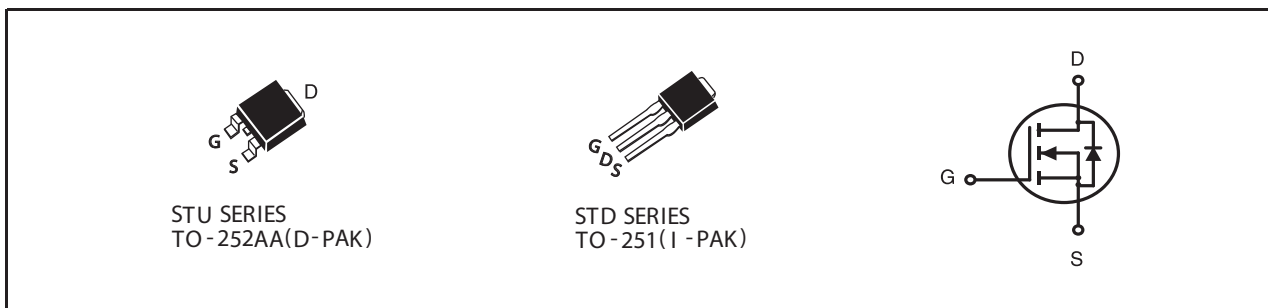


**N-Channel Logic Level Enhancement Mode Field Effect Transistor**

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
40V	50A	9 @ V _{GS} =10V
		11 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- TO-252 and TO-251 Package.

**ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)**

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^a	T _C =25°C	50
		T _C =70°C	40
I _{DM}	-Pulsed ^b	147	A
I _{AS}	Single Pulse Avalanche Current ^d	23	A
E _{AS}	Single Pulse Avalanche Energy ^d	130	mJ
P _D	Maximum Power Dissipation ^a	T _C =25°C	42
		T _C =70°C	27
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θ JC}	Thermal Resistance, Junction-to-Case ^a	3	°C/W
R _{θ JA}	Thermal Resistance, Junction-to-Ambient ^a	50	°C/W

STU/D432S

Ver 1.1

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =32V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{bs} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1.25	1.6	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =10A		7	9	m ohm
		V _{GS} =4.5V , I _D =5A		9	11	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =10A		28		S
DYNAMIC CHARACTERISTICS ^c						
C _{ISS}	Input Capacitance	V _{DS} =15V, V _{GS} =0V f=1.0MHz		1130		pF
C _{OSS}	Output Capacitance			240		pF
C _{RSS}	Reverse Transfer Capacitance			145		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =15V I _D =1A V _{GS} =10V R _{GEN} =3.3 ohm		18		ns
t _r	Rise Time			22		ns
t _{D(OFF)}	Turn-Off Delay Time			61		ns
t _f	Fall Time			9.6		ns
Q _g	Total Gate Charge	V _{DS} =15V, I _D =10A, V _{GS} =10V		23.5		nC
		V _{DS} =15V, I _D =10A, V _{GS} =4.5V		11.5		nC
Q _{gs}	Gate-Source Charge	V _{DS} =15V, I _D =10A, V _{GS} =10V		2.7		nC
Q _{gd}	Gate-Drain Charge			3.2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _s	Maximum Continuous Drain-Source Diode Forward Current				20	A
V _{SD}	Diode Forward Voltage ^b	V _{GS} =0V, I _s =20A		0.91	1.3	V

Notes

- Surface Mounted on FR4 Board, t ≤ 10sec.
- Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Starting T_J=25°C, L=0.5mH, V_{DD} = 20V. (See Figure13)

Nov, 18, 2008

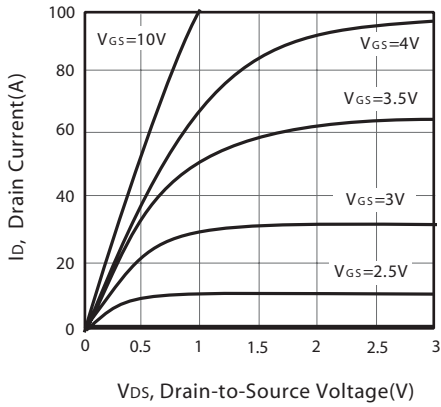


Figure 1. Output Characteristics

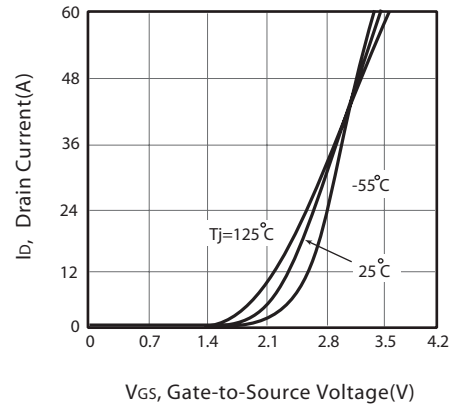


Figure 2. Transfer Characteristics

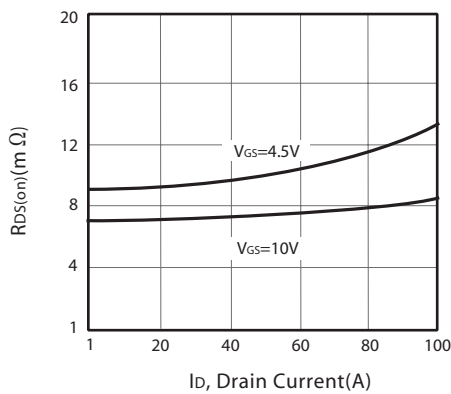


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

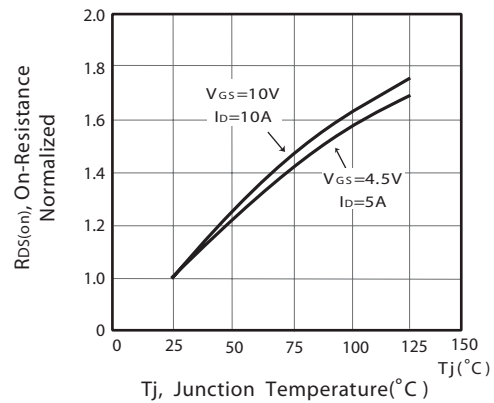


Figure 4. On-Resistance Variation with Drain Current and Temperature

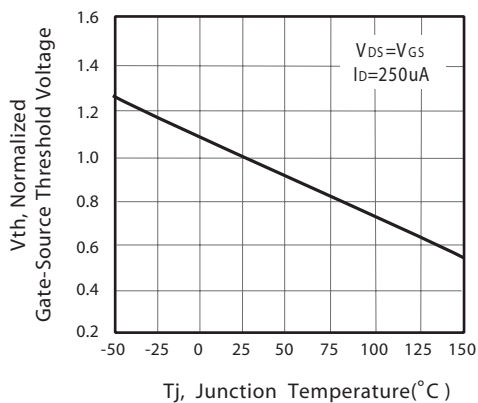


Figure 5. Gate Threshold Variation with Temperature

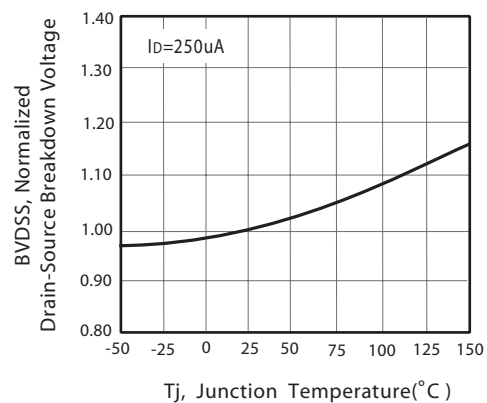


Figure 6. Breakdown Voltage Variation with Temperature

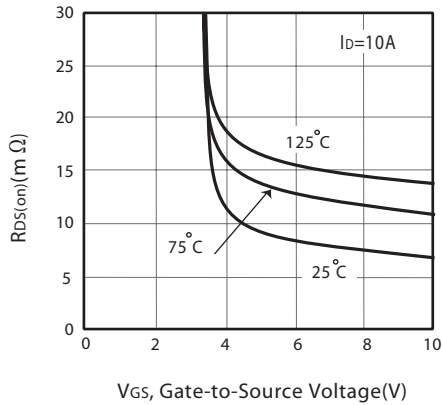


Figure 7. On-Resistance vs. Gate-Source Voltage

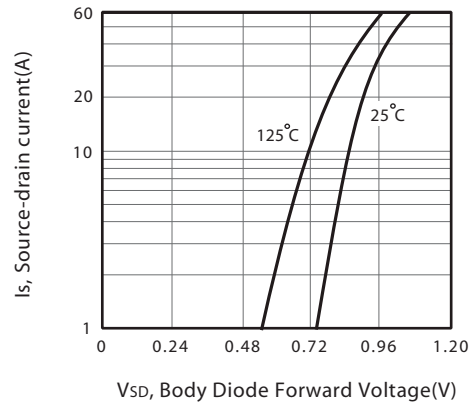


Figure 8. Body Diode Forward Voltage Variation with Source Current

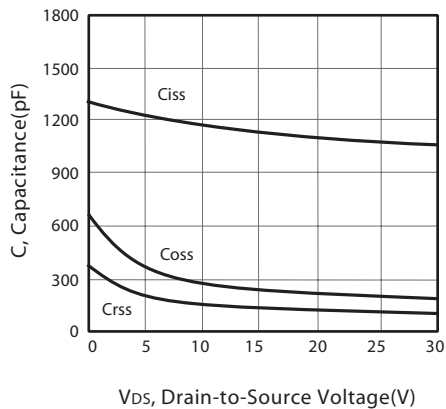


Figure 9. Capacitance

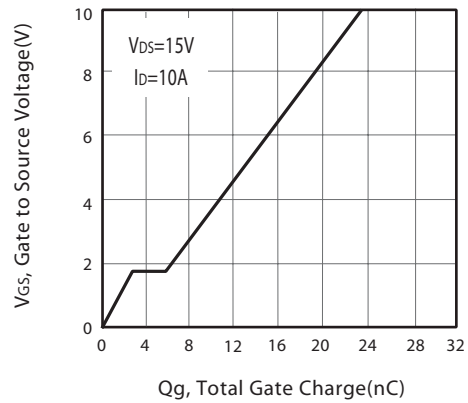


Figure 10. Gate Charge

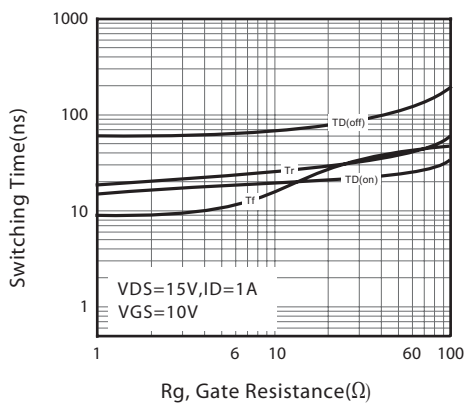


Figure 11. switching characteristics

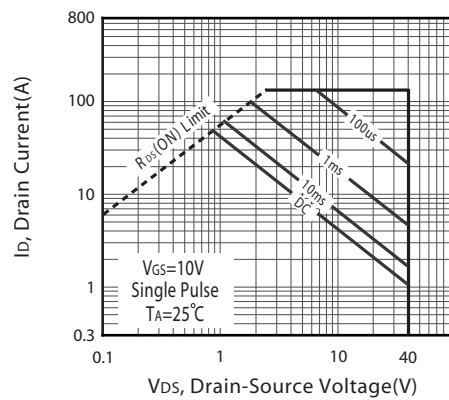
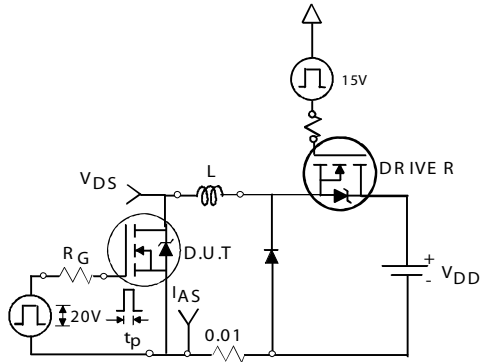
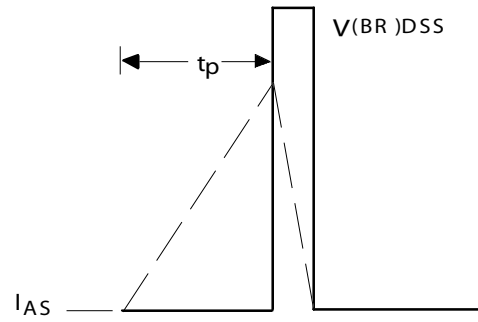


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

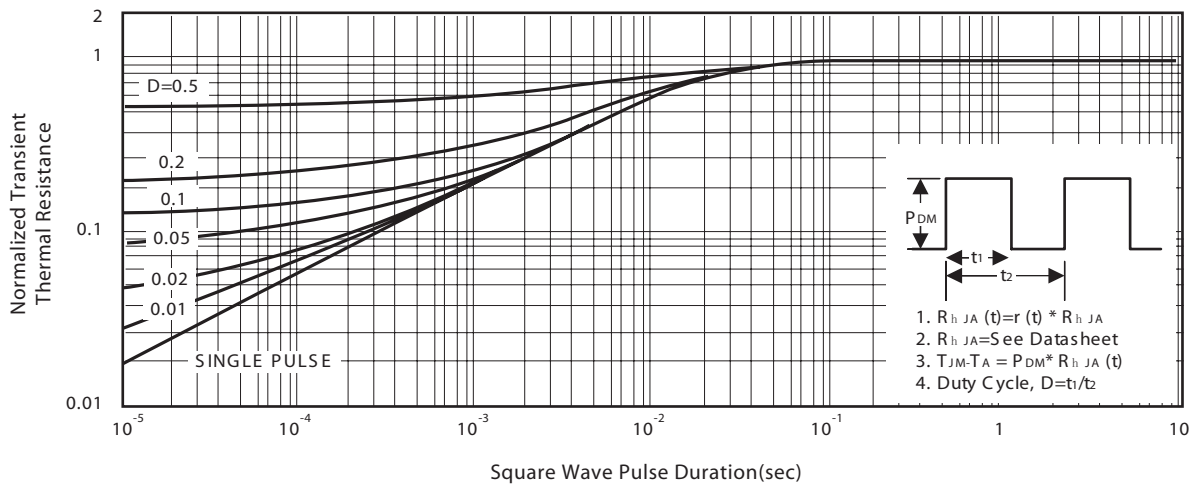
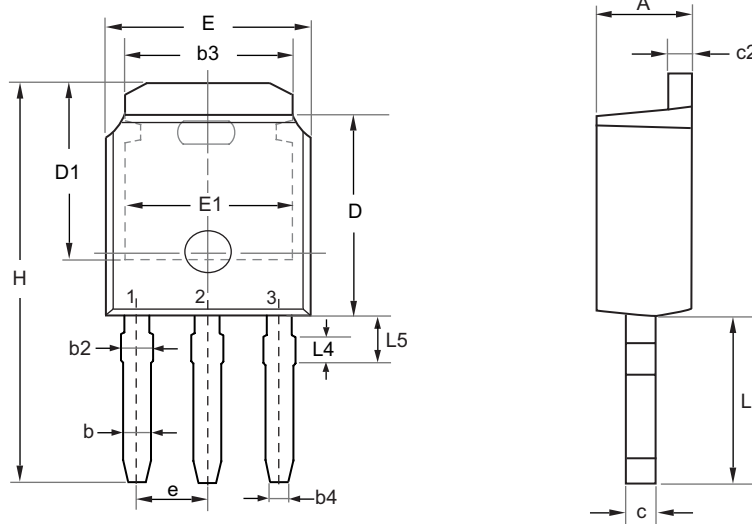


Figure 14. Normalized Thermal Transient Impedance Curve

PACKAGE OUTLINE DIMENSIONS

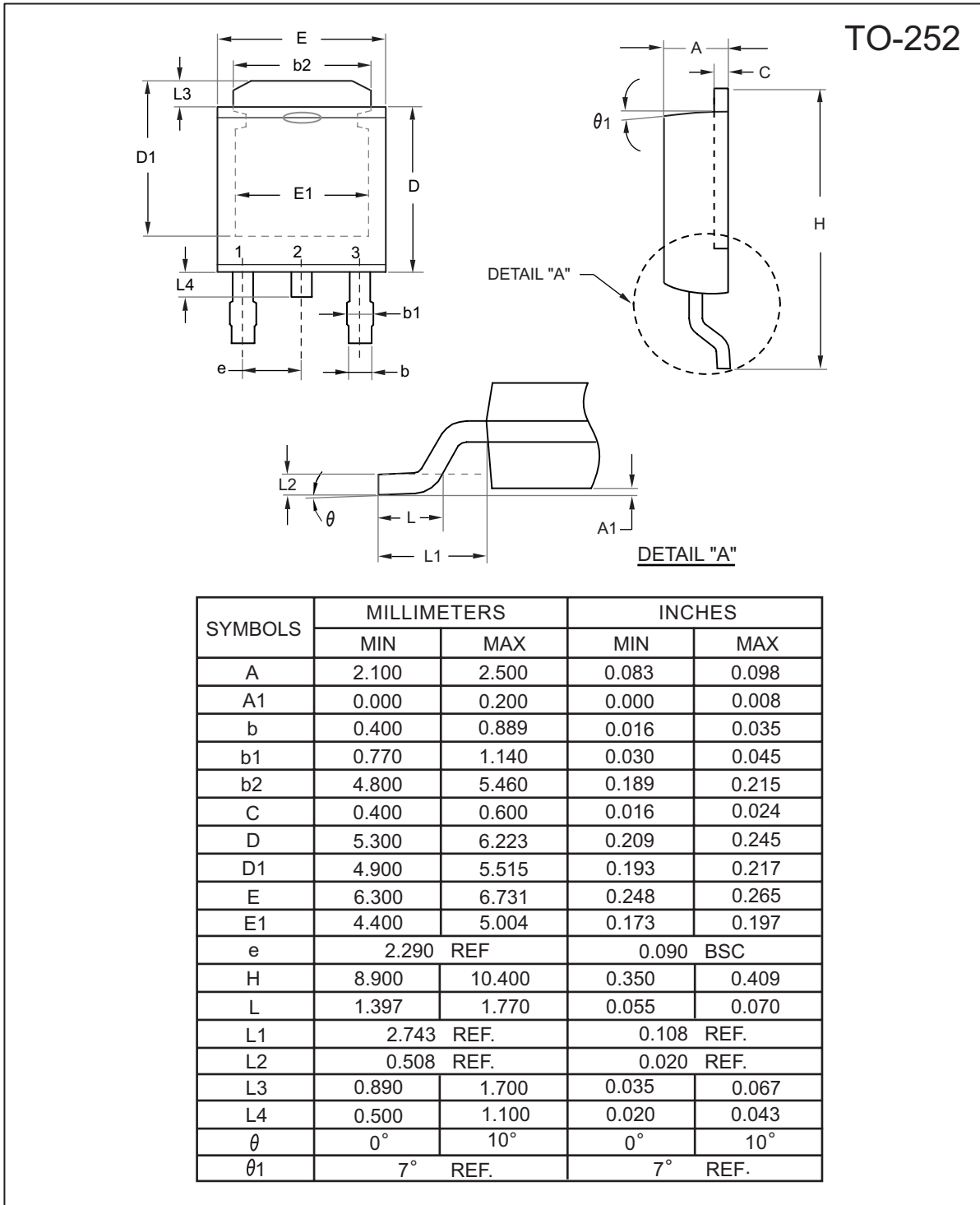
TO-251



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
E	6.400	6.731	0.252	0.265
L	3.980	4.280	0.157	0.169
L4	0.698 REF		0.027 REF	
L5	0.972	1.226	0.038	0.048
D	6.000	6.223	0.236	0.245
H	11.050	11.450	0.435	0.450
b	0.640	0.880	0.025	0.035
b2	0.770	1.140	0.030	0.045
b3	5.210	5.460	0.205	0.215
b4	0.450	0.550	0.018	0.022
e	2.286 BSC		0.090 BSC	
A	2.200	2.380	0.087	0.094
c	0.400	0.600	0.016	0.024
c2	0.400	0.600	0.016	0.024
D1	5.100	---	0.201	---
E1	4.400	---	0.173	---

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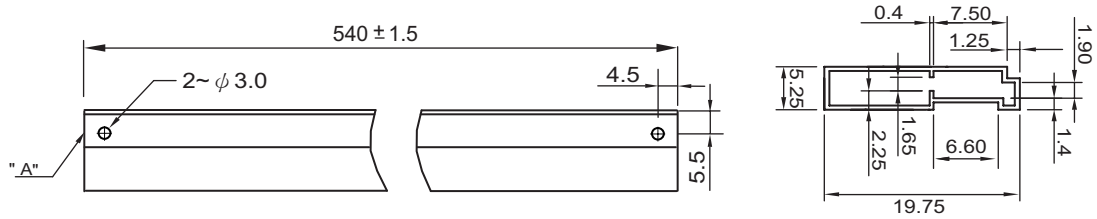
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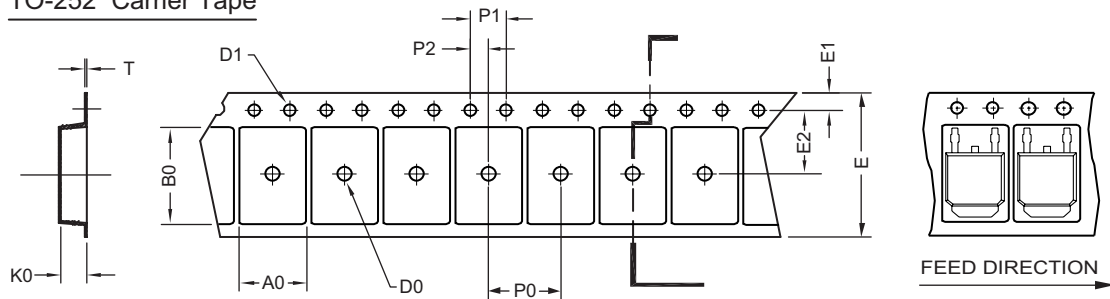
Nov,18,2008

TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



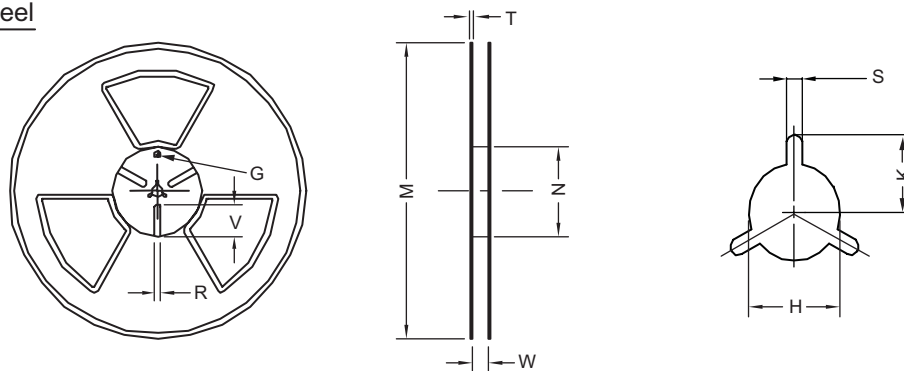
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---